

DESCRIPTION

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CONDUCTOR

TS19501CB10H is a single channel LED driver of lowside-current sense. This device can operate in DCM, BCM and CCM mode with full protection and diagnostics. This device is dedicated and suited for automotive headlight. This controller supports typical topologies such as boost, buck-boost and SEPIC.

Output current regulation is based on average current mode control supervised by a control loop. The fault flag is connected to pull-up resistor from V_{DC} for highlighting the information of fault and fault status flag is latched by the timer when output is low.

APPLICATION

- Automotive LED Lighting: High and low Beam, Daytime Running Light, Turn indicator, Position Light, Fog Light
- General Lighting Applications
- High Brightness LED Applications

FEATURES

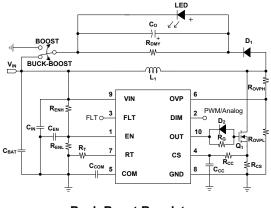
- AEC-Q100 qualified with the following results:
 - Device temperature grade 1: -40°C to 125°C
 - Device HBM ESD classification level H2
 - Device CDM ESD classification level C6
- Drives LEDs in Boost, Buck-Boost and SEPIC Topology
- Operation in DCM, BCM, CCM mode
- Input Voltage 4.5V ~ 42V
- Adjustable Switching Frequency 70k ~ 700kHz
- Low-Side Current Sense
- Internal Voltage Reference 150mV ±3.3%
- Both PWM Dimming and Analog Dimming
- Over Voltage Protection (OVP)
- Over Current Protection (OCP)
- Over Temperature Protection (OTP)
- Under Voltage Lockout (UVLO)
- Jitter function for effective spread spectrum to reduce EMI
- Fault Status flag and Internal Soft Start
- to RoHS Compliant
- Halogen-Free according to IEC 61249-2-21





Notes: MSL 3 (Moisture Sensitivity Level) per J-STD-020

TYPICAL APPLICATION CIRCUIT

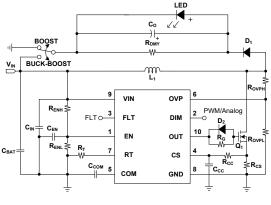


Buck-Boost Regulator

Pin Definition:

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1. EN	10. OUT
2. DIM	9. VIN
3. FLT	8. GND
4. CS	7. RT
5. COM	6. OVP



Boost Regulator



PARAMETER	SYMBOL	LIMIT	UNIT
Battery power input Pin	V _{IN}	-0.3 to 42	V
FLT output to GND	V _{FLT}	-0.3 to 42	V
OUT voltage to GND	V _{OUT}	-0.3 to 20	V
EN voltage to GND	V _{EN}	-0.3 to 5.5	V
DIM voltage to GND	V _{DIM}	-0.3 to 5.5	V
CS voltage to GND	V _{CS}	-0.3 to 5.5	V
COM voltage to GND	V _{COM}	-0.3 to 5.5	V
OVP voltage to GND	V _{OVP}	-0.3 to 5.5	V
RT voltage to GND	V _{RT}	-0.3 to 5.5	V
Junction Temperature Range	TJ	-40 to +150	°C
Storage Temperature Range	T _{STG}	-65 to +150	°C
Lead Temperature (Soldering 10 sec)	T _{LEAD}	260	°C
Power Dissipation @ T _A =25°C	P _D	1.1	W
ESD Rating (Human Body Model)	HBM	±2	kV
ESD Rating (Charged Device Model)	CDM	±1	kV

THERMAL PERFORMANCE (Note 2)				
PARAMETER	SYMBOL	ТҮР	UNIT	
Thermal Resistance Junction to Ambient	R _{θJA}	113	°C/W	
Thermal Resistance Junction to Case	$R_{ ext{ ext{ heta}JC}}$	38	°C/W	

RECOMMENDED OPERATING CONDITION ($T_A = 25^{\circ}C$ unless otherwise specified) (Note 3)				
PARAMETER	SYMBOL	LIMIT	UNIT	
Battery power input Pin	V _{IN}	8 to 38	V	
FLT output to GND	V _{FLT}	0 to 38	V	
OUT voltage to GND	V _{OUT}	0 to 18	V	
EN voltage to GND	V _{EN}	0 to 5	V	
DIM voltage to GND	V _{DIM}	0 to 5	V	
CS voltage to GND	V _{CS}	0 to 0.8	V	
COM voltage to GND	V _{COM}	1.2 to 3.6	V	
OVP voltage to GND	V _{OVP}	1.6 to 3.1	V	
RT voltage to GND	V _{RT}	1.2	V	
Storage Temperature Range	T _{STG}	-55 to +150	°C	
Operating Junction Temperature Range	TJ	-40 to +150	°C	
Operating Ambient Temperature Range	T _{OPA}	-40 to +125	°C	



PARAMETER	SYMBOL	CONDITION	MIN	ТҮР	MAX	UNIT
Supply Voltage						
V _{IN} Turn-on Threshold	V _{IN_ON}		3.8	4.3	4.8	V
V _{IN} Hysteresis	V _{HYS}			0.2		V
EN Turn-on Threshold	V _{EN_ON}		1.05		1.35	V
EN Hysteresis Current	I _{HYS_EN}		10	20	30	μA
Quiescent Current	Ι _Q		80	160	240	μA
Operating Supply Current	I _{IN}	R _{RT} =50kohm	1		4	mA
GM Amplifier	·	·				
Internal Reference Voltage	V _{REF}		140	150	160	mV
Transconductance	G _m	I _{COM_SINK} /0.4	80	100	120	μA/V
Sink Current	I _{COM_SINK}	V _{CS} = 400mV		40		μA
Source Current	I _{COM_SOUR}	V _{CS} = 0V		15		μA
Oscillator	·	·				
Oscillator Frequency	Fosc	R _{RT} =50kohm	185	200	215	kHz
Jitter Frequency	F _{JT}	Design Guarantee		±8.5		%
Soft Start Time	T _{ss}			1024		
Fault Blank Time	T _{FB}			2048		Clock Cycles
Hiccup Time	T _{HUP}			32768		
Driver	·	·				
Dropout Voltage	V _{OH}	VIN=12V, C _O =1nF IO= 10mA		530	700	mV
Diopout voltage	V _{OL}	V _{IN} =12V, C _O =1nF I _O = -10mA		50	90	mV
Output Rising Time	T _R	C _o =1nF		40		ns
Output Falling Time	T _F	C _o =1nF		30	-	ns
Output Clamp Voltage	V_{O_CLAMP}	C _o =1nF		12.5	12.8	V
Protection						
Output Voltage Protection	V _{OVP}		3.0	3.25	3.5	V
Short Circuit Protection	V _{SCP}		1.4		1.6	V
Current Limit Voltage	V _{CSL}		720	820	920	mV
Leading Edge Blanking Time	LEBt	C _o =1nF		350	500	ns
MOS Current Protection	V _{MCP}	C _o =1nF	1.1	1.23	1.4	V
FLT Dropout Voltage	V _{FLT}	I _{FLT} =10mA		200		mV
Maximum Duty	V _{DUTY}	C _o =1nF		85		%



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ELECTRICAL SPECIFICATIONS (T _A = 25°C unless otherwise specified)					
SYMBOL	CONDITION	MIN	ТҮР	MAX	UNIT
Vон_dim		2.5			V
Vmax_dima		1.5	1.6	1.7	V
Ілм		7.2	10	12.8	μA
Thermal Section (Note 4, 5)					
TSD			165		°C
T _{HYS}			30		°C
	SYMBOL Voh_dim Vmax_dima Idim TSD	SYMBOL CONDITION Voh_dim Vmax_dima Idim	SYMBOL CONDITION MIN Voh_dim 2.5 Vmax_dima 1.5 Idim 7.2 TSD	SYMBOL CONDITION MIN TYP VOH_DIM 2.5 VMAX_DIMA 1.5 1.6 IDIM 7.2 10 TSD 165	SYMBOL CONDITION MIN TYP MAX VOH_DIM 2.5 VMAX_DIMA 1.5 1.6 1.7 IDIM 7.2 10 12.8 TSD 165

Note:

1. Stresses listed as the above "Absolute Maximum Ratings" may cause permanent damage to the device. Functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

- 2. Test boards conditions:
 - (a) 5.6mm × 4mm, 2 layers, thickness: 1mm.
 - (b) 1-oz copper traces located on the top of the PCB.
 - (c) 1-oz copper ground plane, bottom layer.
 - (d) 5-thermal vias (0.3mm) located under the device package.
- 3. The device is not guaranteed to function outside its operating conditions.
- 4. Guaranteed by design.
- 5. Auto Recovery type.

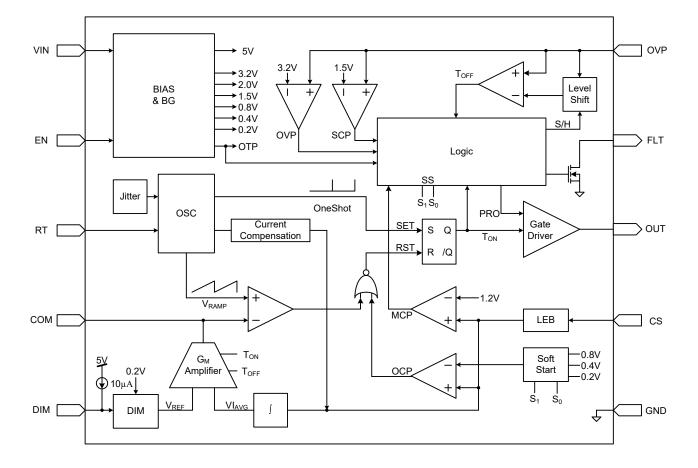
ORDERING INFORMATION

ORDERING CODE	PACKAGE	PACKING
TS19501CB10H RBG	MSOP-10EP	5,000pcs / 13"Reel



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FUNCTION BLOCK



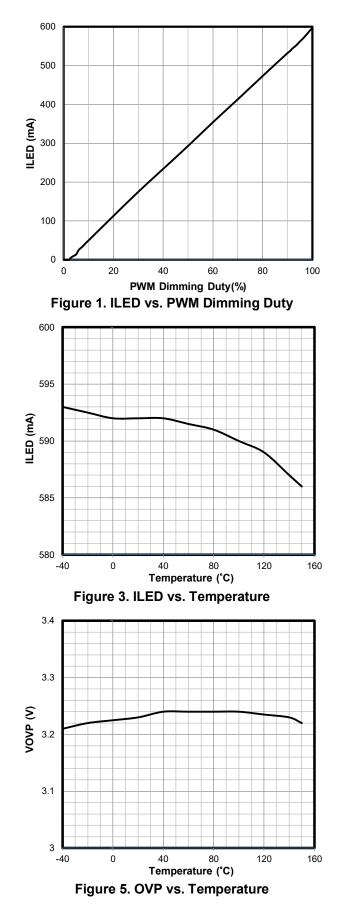
PIN DESCRIPTION

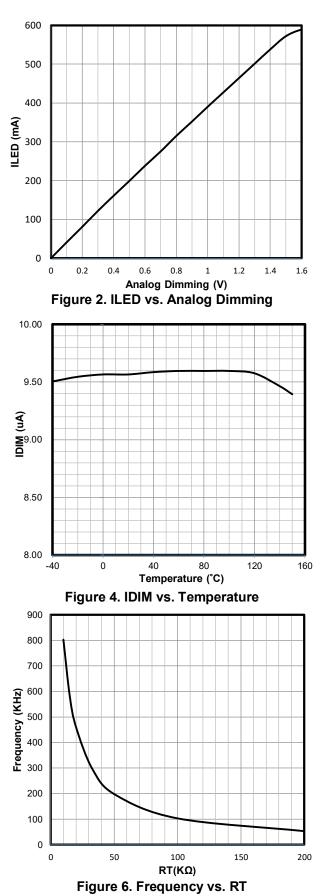
PIN NO.	NAME	FUNCTION
1	EN	Enable and shut down pin
2	DIM	PWM/Analog dimming voltage input
3	FLT	Open drain output pin for fault status flag.
4	CS	Input current sense pin.
5	COM	Compensation output pin of error amplifier.
6	OVP	Over voltage sensing pin
7	RT	Connect external resistor to GND to set frequency.
8	GND	Ground return for all internal circuitry.
9	VIN	Battery power input pin for all internal circuitry.
10	OUT	Power MOS output pin.
Thermal pad No internal connection		No internal connection

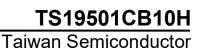


TYPICAL PERFORMANCE CURVES

 V_{IN} =12V, I_{LED} =600mA, V_{O} =24V (8 LEDs) unless otherwise specified.

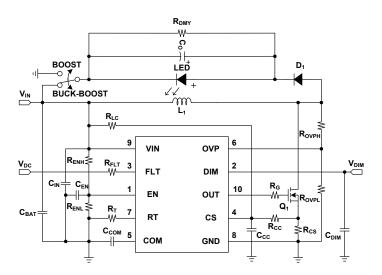




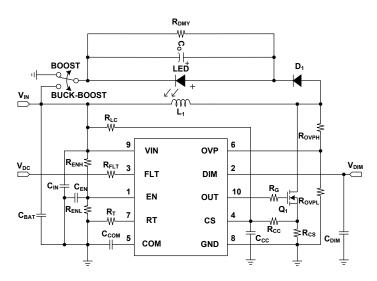




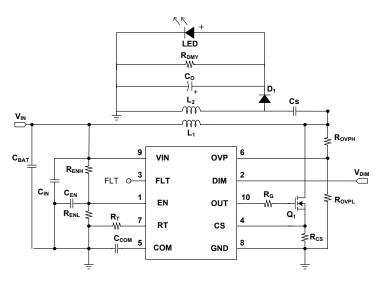
TYPICAL APPLICATION CIRCUITS



Buck-Boost Regulator







SEPIC



APPLICATION INFORMATION

The TS19501CB10H uses an external current sense resistor (R_{CS}) between the MOSFET source and the GND to convert the input power. The MOSFET ON current signal and V_{REF} are input to the GM amplifier. The special GM amplifier follows the design formula to combine the T_{ON} and T_{OFF} information which are forced to be equal potential through system negative feedback.

The average LED current can be expressed as below.

$$I_{LED_avg} = \frac{V_{REF}}{R_{CS}}$$

Where:

- I_{LED_avg} is the average LED current
- V_{REF} is the internal reference voltage (150mV)
- R_{cs} is the sensing resistor connected between the MOSFET source and the GND

Pin Definitions

EN Pin

The EN pin can sense V_{IN} information by voltage divider resister. The hysteresis current (I_{EN}) is 20µA when the divider voltage is over V_{EN_ON} .

DIM Pin

A PWM and analog dimming function is applied in TS19501CB10H. The analog dimming range is an DC voltage from 0V to 1.6V. PWM dimming function is the same pin of analog dimming. The current regulation is decided by duty cycle of external PWM signal. Built-in 10µA source current is for NTC resistance application.

FLT Pin

Open drain output for fault status flag.

CS Pin

MOSFET current signal sensing and current limit setting function.

$$I_{CS(LIMIT)} = \frac{0.8}{R_{CS}}$$

Where:

- I_{CS(LIMIT)} is the input current limit
- R_{cs} is the sensing resistor connected between the MOSFET source and GND

COM Pin

This is the output of the G_m amplifier. Connect with a suitable RC network to ground.



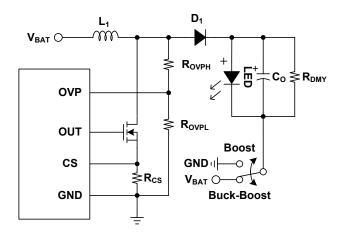
APPLICATION INFORMATION

Pin Definitions (Continue)

OVP Pin

The Output voltage is reflected by inductor voltage. The OVP pin can sense output information which it departs from start-up voltage (V_{SCP}) and protect voltage (V_{OVP}).

When the OVP sense voltage under V_{SCP} a period of time (8 clock cycles), The short circuit protection (SCP) will work. When the OVP sense voltage over V_{OVP} a period of time (8 clock cycles), the over voltage protection (OVP) will work. it will attempt to recover after every 32768 clock cycles.



For Boost

$$Vo_{o_{P}} = 3.2 \times \frac{Rov_{PH} + Rov_{PL}}{Rov_{PL}}$$
$$Vo_{sCP} = 1.5 \times \frac{Rov_{PH} + Rov_{PL}}{Rov_{PL}}$$

For Buck-Boost and SEPIC

$$Vo_{o_{P}} = \left(3.2 \times \frac{R_{OVPH} + R_{OVPL}}{R_{OVPL}}\right) - V_{BAT}$$
$$Vo_{SCP} = \left(1.5 \times \frac{R_{OVPH} + R_{OVPL}}{R_{OVPL}}\right) - V_{BAT}$$

Where:

- V_{OVP} is the output-over-voltage protection point (3.2V)
- V_{SCP} is the output-short-circuit protection point (1.5V)

<u>RT Pin</u>

This pin is to program the operation frequency by connecting a resistor to ground. Reference formula as below:

$$F_S = \frac{1}{1 \times 10^{-10} \times R_T}$$

GND Pin

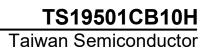
GND is the reference node of internal circuit.

VIN Pin

Power supply input for the controller during normal operation. The controller will start up when V_{IN} reaches 4.2V (typical) and will shut-down when V_{IN} voltage is below 4.0V (typical) when V_{EN} over 1.2V. A decoupling capacitor should be connected between the V_{IN} and GND pin as close as possible.

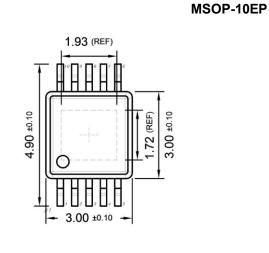
OUT Pin

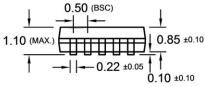
Gate drive for external MOSFET switch and built-in gate clamp function.

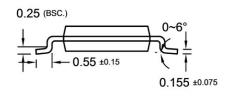




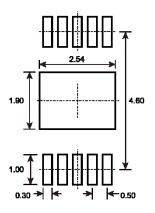
PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)



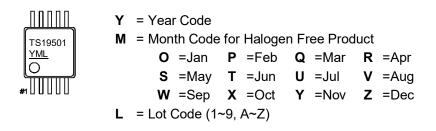




SUGGESTED PAD LAYOUT (Unit: Millimeters)



MARKING DIAGRAM





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